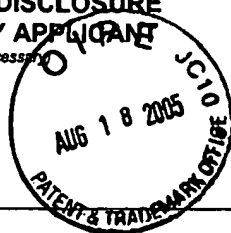


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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	10/789,044
Filing Date	February 27, 2004
First Named Inventor	Ahn, Kie
Group Art Unit	2891
Examiner Name	Menz, Douglas

Sheet 1 of 2

Attorney Docket No: 1303.070US2

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STATEMENT BY APPLICANT**

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Sheet 2 of 2

Attorney Docket No: 1303.070US2

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